

Dae Hwan Kim

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

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|--------------------|-------------------------|----------------|-----------------|
| 136 papers | 2,153 citations | 25 h-index | 41 g-index |
| 138 ext. papers | 2,484 ext. citations | 3.7 avg, IF | 4.66 L-index |

| # | Paper | IF | Citations |
|-----|--|-----|-----------|
| 136 | Influence of Al ₂ O ₃ layer on InGaZnO memristor crossbar array for neuromorphic applications. <i>Chaos, Solitons and Fractals</i> , 2022 , 156, 111813 | 9.3 | 2 |
| 135 | Effect of Hydrogen Migration in SiO ₂ /Al ₂ O ₃ Stacked Gate Insulator of InGaZnO Thin-Film Transistors. <i>Crystals</i> , 2022 , 12, 594 | 2.3 | 2 |
| 134 | Electrode-dependent electrical switching characteristics of InGaZnO memristor. <i>Chaos, Solitons and Fractals</i> , 2022 , 158, 112106 | 9.3 | 0 |
| 133 | Temperature and gate-bias-dependent charge transport in inkjet-printed polymer field-effect transistor. <i>Journal of the Korean Physical Society</i> , 2021 , 79, 1063-1068 | 0.6 | 0 |
| 132 | Total Subgap Range Density of States-Based Analysis of the Effect of Oxygen Flow Rate on the Bias Stress Instabilities in a-IGZO TFTs. <i>IEEE Transactions on Electron Devices</i> , 2021 , 1-8 | 2.9 | 5 |
| 131 | Multiplexed Silicon Nanowire Tunnel FET-Based Biosensors With Optimized Multi-Sensing Currents. <i>IEEE Sensors Journal</i> , 2021 , 21, 8839-8846 | 4 | 2 |
| 130 | Reliability-Aware SPICE Compatible Compact Modeling of IGZO Inverters on a Flexible Substrate. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 4838 | 2.6 | 2 |
| 129 | Observation of Hydrogen-Related Defect in Subgap Density of States and Its Effects Under Positive Bias Stress in Amorphous InGaZnO TFT. <i>IEEE Electron Device Letters</i> , 2021 , 42, 708-711 | 4.4 | 7 |
| 128 | Impact Ionization and Hot-Carrier Degradation in Saddle-Fin and Buried-Gate Transistor of Dynamic Random Access Memory at Cryogenic Temperature. <i>IEEE Electron Device Letters</i> , 2021 , 42, 653-656 | 4.4 | 1 |
| 127 | Observation of Divacancy Formation for ZnON Thin-Film Transistors With Excessive N Content. <i>IEEE Electron Device Letters</i> , 2021 , 42, 1006-1009 | 4.4 | 0 |
| 126 | . <i>IEEE Access</i> , 2021 , 9, 73090-73102 | 3.5 | 2 |
| 125 | Humidity Effects According to the Type of Carbon Nanotubes. <i>IEEE Access</i> , 2021 , 9, 6810-6816 | 3.5 | 5 |
| 124 | Analysis of Threshold Voltage Shift for Full V/V/Oxygen-Content Span under Positive Bias Stress in Bottom-Gate Amorphous InGaZnO Thin-Film Transistors. <i>Micromachines</i> , 2021 , 12, | 3.3 | 3 |
| 123 | Effect of the Gate Dielectric Layer of Flexible InGaZnO Synaptic Thin-Film Transistors on Learning Behavior. <i>ACS Applied Electronic Materials</i> , 2021 , 3, 3972-3979 | 4 | 9 |
| 122 | Fabrication of Circadian Light Meter with Non-Periodic Optical Filters to Evaluate the Non-Visual Effects of Light on Humans. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 8283 | 2.6 | 0 |
| 121 | Current-to-transconductance ratio technique for simultaneous extraction of threshold voltage and parasitic resistances in MOSFETs. <i>Solid-State Electronics</i> , 2021 , 183, 108133 | 1.7 | 1 |
| 120 | Modeling and characterization of photovoltaic and photoconductive effects in insulated-gate field effect transistors under optical excitation. <i>Solid-State Electronics</i> , 2021 , 186, 108139 | 1.7 | |

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| 119 | Threshold-Variation-Tolerant Coupling-Gate HfGZO Synaptic Transistor for More Reliably Controllable Hardware Neuromorphic System. <i>IEEE Access</i> , 2021 , 9, 59345-59352 | 3.5 | 3 |
| 118 | Experimental extraction of stern-layer capacitance in biosensor detection using silicon nanowire field-effect transistors. <i>Current Applied Physics</i> , 2020 , 20, 828-833 | 2.6 | 11 |
| 117 | Complementary Hybrid Semiconducting Superlattices with Multiple Channels and Mutual Stabilization. <i>Nano Letters</i> , 2020 , 20, 4864-4871 | 11.5 | 7 |
| 116 | Hybrid integration of carbon nanotube and amorphous IGZO thin-film transistors. <i>AIP Advances</i> , 2020 , 10, 025131 | 1.5 | 4 |
| 115 | Influence of Nitrogen Content on Persistent Photoconductivity in Zinc Oxynitride Thin Film Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 41, 561-564 | 4.4 | 1 |
| 114 | Wafer-scale carbon nanotube network transistors. <i>Nanotechnology</i> , 2020 , 31, 465303 | 3.4 | 1 |
| 113 | Hydrophobic Polymer Encapsulation Effects on Subgap Density of States in Multilayered Molybdenum Disulfide Field-Effect Transistors. <i>Physica Status Solidi - Rapid Research Letters</i> , 2020 , 14, 1900492 | 2.5 | 3 |
| 112 | Positive Bias Stress Instability of InGaZnO TFTs With Self-Aligned Top-Gate Structure in the Threshold-Voltage Compensated Pixel. <i>IEEE Electron Device Letters</i> , 2020 , 41, 50-53 | 4.4 | 3 |
| 111 | Density-of-States-Based Physical Model for Ink-Jet Printed Thiophene Polymeric TFTs. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 283-288 | 2.9 | 0 |
| 110 | Alternating Current-Based Technique for Separate Extraction of Parasitic Resistances in MISFETs With or Without the Body Contact. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1528-1531 | 4.4 | 2 |
| 109 | A highly reliable physics-based SPICE compact model of IGZO memristor considering the dependence on electrode metals and deposition sequence. <i>Solid-State Electronics</i> , 2020 , 166, 107764 | 1.7 | 0 |
| 108 | Effect of Anion Composition on the Bias Stress Stability in Zn-O-N Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1376-1379 | 4.4 | 0 |
| 107 | One Transistor-Two Memristor Based on Amorphous Indium-Gallium-Zinc-Oxide for Neuromorphic Synaptic Devices. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2837-2844 | 4 | 9 |
| 106 | Pd/IGZO/p+-Si Synaptic Device with Self-Graded Oxygen Concentrations for Highly Linear Weight Adjustability and Improved Energy Efficiency. <i>ACS Applied Electronic Materials</i> , 2020 , 2, 2390-2397 | 4 | 8 |
| 105 | Extraction Technique for Flat Band Voltage Using Multi-Frequency C _{IV} Characteristics in Amorphous InGaZnO Thin-Film-Transistors. <i>IEEE Electron Device Letters</i> , 2020 , 41, 1778-1781 | 4.4 | 0 |
| 104 | 73-3: Invited Paper: Influences of Circadian Illuminances from Lighting and TV on the Human Locomotor Activity, Sleep Disorder, EEG, HRV, and Melatonin Secretion. <i>Digest of Technical Papers SID International Symposium</i> , 2020 , 51, 1094-1097 | 0.5 | |
| 103 | Digital and Analog Switching Characteristics of InGaZnO Memristor Depending on Top Electrode Material for Neuromorphic System. <i>IEEE Access</i> , 2020 , 8, 192304-192311 | 3.5 | 11 |
| 102 | Deep depletion capacitance-voltage technique for spatial distribution of traps across the substrate in MOS structures. <i>Solid-State Electronics</i> , 2020 , 173, 107905 | 1.7 | |

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| 101 | Effect of Oxygen Content on Current Stress-Induced Instability in Bottom-Gate Amorphous InGaZnO Thin-Film Transistors. <i>Materials</i> , 2019 , 12, | 3.5 | 25 |
| 100 | Oxygen Content and Bias Influence on Amorphous InGaZnO TFT-Based Temperature Sensor Performance. <i>IEEE Electron Device Letters</i> , 2019 , 40, 1666-1669 | 4.4 | 5 |
| 99 | Control of the Boundary between the Gradual and Abrupt Modulation of Resistance in the Schottky Barrier Tunneling-Modulated Amorphous Indium-Gallium-Zinc-Oxide Memristors for Neuromorphic Computing. <i>Electronics (Switzerland)</i> , 2019 , 8, 1087 | 2.6 | 11 |
| 98 | Effect of Simultaneous Mechanical and Electrical Stress on the Electrical Performance of Flexible In-Ga-Zn-O Thin-Film Transistors. <i>Materials</i> , 2019 , 12, | 3.5 | 10 |
| 97 | . <i>IEEE Electron Device Letters</i> , 2019 , 40, 40-43 | 4.4 | 4 |
| 96 | Implementing an artificial synapse and neuron using a Si nanowire ion-sensitive field-effect transistor and indium-gallium-zinc-oxide memristors. <i>Sensors and Actuators B: Chemical</i> , 2019 , 296, 1266-1276 | 8.5 | 8 |
| 95 | P-3: A Study on the Hot Carrier Effect in InGaZnO Thin Film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2019 , 50, 1222-1225 | 0.5 | 16 |
| 94 | ZnO composite nanolayer with mobility edge quantization for multi-value logic transistors. <i>Nature Communications</i> , 2019 , 10, 1998 | 17.4 | 39 |
| 93 | . <i>IEEE Electron Device Letters</i> , 2019 , 40, 1431-1434 | 4.4 | 4 |
| 92 | Flexible carbon nanotube Schottky diode and its integrated circuit applications.. <i>RSC Advances</i> , 2019 , 9, 22124-22128 | 3.7 | 6 |
| 91 | Ultrasensitive Electrical Detection of Hemagglutinin for Point-of-Care Detection of Influenza Virus Based on a CMP-NANA Probe and Top-Down Processed Silicon Nanowire Field-Effect Transistors. <i>Sensors</i> , 2019 , 19, | 3.8 | 16 |
| 90 | Method to Extract Interface and Bulk Trap Separately Over the Full Sub-Gap Range in Amorphous InGaZnO Thin-Film Transistors by Using Various Channel Thicknesses. <i>IEEE Electron Device Letters</i> , 2019 , 40, 574-577 | 4.4 | 12 |
| 89 | SPICE compact model of IGZO memristor based on non-quasi statically updated Schottky barrier height 2019 , | | 2 |
| 88 | The Calculation of Negative Bias Illumination Stress-Induced Instability of Amorphous InGaZnO Thin-Film Transistors for Instability-Aware Design. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1002-1008 | 2.0 | 8 |
| 87 | Synaptic devices based on two-dimensional layered single-crystal chromium thiophosphate (CrPS4). <i>NPG Asia Materials</i> , 2018 , 10, 23-30 | 10.3 | 35 |
| 86 | A novel fabrication method for co-integrating ISFET with damage-free sensing oxide and threshold voltage-tunable CMOS read-out circuits. <i>Sensors and Actuators B: Chemical</i> , 2018 , 260, 627-634 | 8.5 | 9 |
| 85 | Impact of Ground Plane Doping and Bottom-Gate Biasing on Electrical Properties in In _{0.53} Ga _{0.47} As-OI MOSFETs and Donor Wafer Reusability Toward Monolithic 3-D Integration With In _{0.53} Ga _{0.47} As Channel. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 1862-1868 | 2.9 | 13 |
| 84 | Effect of oxygen content of the LaAlO ₃ layer on the synaptic behavior of Pt/LaAlO ₃ /Nb-doped SrTiO ₃ memristors for neuromorphic applications. <i>Solid-State Electronics</i> , 2018 , 140, 139-143 | 1.7 | 16 |

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| 83 | Universal model of bias-stress-induced instability in inkjet-printed carbon nanotube networks field-effect transistors. <i>Solid-State Electronics</i> , 2018 , 140, 80-85 | 1.7 | 3 |
| 82 | The electron trap parameter extraction-based investigation of the relationship between charge trapping and activation energy in IGZO TFTs under positive bias temperature stress. <i>Solid-State Electronics</i> , 2018 , 140, 90-95 | 1.7 | 8 |
| 81 | Effect of liquid gate bias rising time in pH sensors based on Si nanowire ion sensitive field effect transistors. <i>Solid-State Electronics</i> , 2018 , 140, 109-114 | 1.7 | 4 |
| 80 | Highly transparent tactile sensor based on a percolated carbon nanotube network. <i>AIP Advances</i> , 2018 , 8, 065109 | 1.5 | 11 |
| 79 | Comprehensive separate extraction of parasitic resistances in MOSFETs considering the gate bias-dependence and the asymmetric overlap length. <i>Microelectronics Reliability</i> , 2018 , 85, 66-70 | 1.2 | 4 |
| 78 | Spectroscopic Influence of Virtual Reality and Augmented Reality Display Devices on the Human Nonvisual Characteristics and Melatonin Suppression Response. <i>IEEE Photonics Journal</i> , 2018 , 1-1 | 1.8 | 2 |
| 77 | 19-3: Late-News Paper: Universal Method to Determine the Dynamic NBIS- and PBS-induced Instabilities on Self-aligned Coplanar InGaZnO Thin-film Transistors. <i>Digest of Technical Papers SID International Symposium</i> , 2018 , 49, 232-235 | 0.5 | 1 |
| 76 | Hybrid complementary inverter based on carbon nanotube and IGZO thin-film transistors with controlled process conditions. <i>Journal of Alloys and Compounds</i> , 2018 , 762, 456-462 | 5.7 | 12 |
| 75 | Three-Dimensional Printed Poly(vinyl alcohol) Substrate with Controlled On-Demand Degradation for Transient Electronics. <i>ACS Nano</i> , 2018 , 12, 6006-6012 | 16.7 | 27 |
| 74 | . <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 3243-3249 | 2.9 | 0 |
| 73 | Synaptic Plasticity Selectively Activated by Polarization-Dependent Energy-Efficient Ion Migration in an Ultrathin Ferroelectric Tunnel Junction. <i>Nano Letters</i> , 2017 , 17, 1949-1955 | 11.5 | 62 |
| 72 | Experimental decomposition of the positive bias temperature stress-induced instability in self-aligned coplanar InGaZnO thin-film transistors and its modeling based on the multiple stretched-exponential functions. <i>Journal of the Society for Information Display</i> , 2017 , 25, 98-107 | 2.1 | 19 |
| 71 | . <i>IEEE Electron Device Letters</i> , 2017 , 38, 584-587 | 4.4 | 6 |
| 70 | Analysis and Modeling on the pH-Dependent Current Drift of Si Nanowire Ion-Sensitive Field Effect Transistor (ISFET)-Based Biosensors. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 3146-3150 | 1.3 | 1 |
| 69 | 21-4: Distinguished Paper: Experimental Decomposition of the Positive Bias Temperature Stress-induced Instability in Self-aligned Coplanar InGaZnO Thin-film Transistors and its Modeling based on the Multiple Stretched-exponential Functions. <i>Digest of Technical Papers SID International Symposium</i> , 2017 , 48, 298-301 | 0.5 | 4 |
| 68 | 7-4: Invited Paper: Internal Compensation Type OLED Display Using High Mobility Oxide TFT. <i>Digest of Technical Papers SID International Symposium</i> , 2017 , 48, 76-79 | 0.5 | 16 |
| 67 | Systematic Decomposition of the Positive Bias Stress Instability in Self-Aligned Coplanar InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2017 , 38, 580-583 | 4.4 | 30 |
| 66 | Band-Bending Effect in the Characterization of Subgap Density-of-States in Amorphous TFTs Through Fully Electrical Techniques. <i>IEEE Electron Device Letters</i> , 2017 , 38, 199-202 | 4.4 | 2 |

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| 65 | Semiconducting carbon nanotube network thin-film transistors with enhanced inkjet-printed source and drain contact interfaces. <i>Applied Physics Letters</i> , 2017 , 111, 173108 | 3-4 | 11 |
| 64 | New Type of Ion-Sensitive Field-Effect Transistor with Sensing Region Separate from Gate-Controlled Region. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 8280-8284 | 1-3 | |
| 63 | Novel Fabrication Method for Forming Damage-Free Sensing Oxide and Threshold Voltage-Tunable Complementary Metal-Oxide Semiconductor in a pH Sensor-CMOS Hybrid System. <i>Journal of Nanoscience and Nanotechnology</i> , 2017 , 17, 8265-8270 | 1-3 | 1 |
| 62 | Transparent, Flexible Strain Sensor Based on a Solution-Processed Carbon Nanotube Network. <i>ACS Applied Materials & Interfaces</i> , 2017 , 9, 26279-26285 | 9-5 | 97 |
| 61 | Enhanced sensing of gas molecules by a 99.9% semiconducting carbon nanotube-based field-effect transistor sensor. <i>Applied Physics Letters</i> , 2017 , 111, 022102 | 3-4 | 12 |
| 60 | Fabrication of InGaAs-on-Insulator Substrates Using Direct Wafer-Bonding and Epitaxial Lift-Off Techniques. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 3601-3608 | 2-9 | 15 |
| 59 | Investigation of Carrier Transport Mechanism in High Mobility ZnON Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2016 , 37, 1570-1573 | 4-4 | 13 |
| 58 | Hybrid Open Drain Method and Fully Current-Based Characterization of Asymmetric Resistance Components in a Single MOSFET. <i>IEEE Transactions on Electron Devices</i> , 2016 , 63, 4196-4200 | 2-9 | 7 |
| 57 | Investigation of Low-Frequency Noise Properties in High-Mobility ZnON Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2016 , 1-1 | 4-4 | |
| 56 | Ink-jet printed semiconducting carbon nanotube ambipolar transistors and inverters with chemical doping technique using polyethyleneimine. <i>Applied Physics Letters</i> , 2016 , 109, 263103 | 3-4 | 11 |
| 55 | Drift-Free pH Detection With Silicon Nanowire Field-Effect Transistors. <i>IEEE Electron Device Letters</i> , 2016 , 37, 652-655 | 4-4 | 9 |
| 54 | Study on the photoresponse of amorphous In-Ga-Zn-O and zinc oxynitride semiconductor devices by the extraction of sub-gap-state distribution and device simulation. <i>ACS Applied Materials & Interfaces</i> , 2015 , 7, 15570-7 | 9-5 | 65 |
| 53 | Bias-Dependent Effective Channel Length for Extraction of Subgap DOS by Capacitance-Voltage Characteristics in Amorphous Semiconductor TFTs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 2689-2694 | 2-9 | 10 |
| 52 | Effect of direct current sputtering power on the behavior of amorphous indium-gallium-zinc-oxide thin-film transistors under negative bias illumination stress: A combination of experimental analyses and device simulation. <i>Applied Physics Letters</i> , 2015 , 106, 123505 | 3-4 | 16 |
| 51 | Dual-Sweep Combinational Transconductance Technique for Separate Extraction of Parasitic Resistances in Amorphous Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2015 , 36, 144-146 | 4-4 | 15 |
| 50 | A Study on the Degradation of In-GaZn-O Thin-Film Transistors Under Current Stress by Local Variations in Density of States and Trapped Charge Distribution. <i>IEEE Electron Device Letters</i> , 2015 , 36, 690-692 | 4-4 | 9 |
| 49 | Extraction of the interface trap density through the differential subthreshold ideality factor technique in normally-off AlGaIn/GaN MOSFETs. <i>Journal of the Korean Physical Society</i> , 2015 , 66, 1291-1294 | 0-6 | 2 |
| 48 | Extraction of Propagation Delay-Related Mobility and Its Verification for Amorphous InGaZnO Thin-Film Transistor-Based Inverters. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 1504-1510 | 2-9 | 3 |

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| 47 | The Effect of Gate and Drain Fields on the Competition Between Donor-Like State Creation and Local Electron Trapping in InGaZnO Thin Film Transistors Under Current Stress. <i>IEEE Electron Device Letters</i> , 2015 , 36, 1336-1339 | 4.4 | 16 |
| 46 | Modeling and Separate Extraction Technique for Gate Bias-Dependent Parasitic Resistances and Overlap Length in MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2015 , 62, 1063-1067 | 2.9 | 5 |
| 45 | Investigation on the negative bias illumination stress-induced instability of amorphous indium-tin-zinc-oxide thin film transistors. <i>Applied Physics Letters</i> , 2014 , 105, 152108 | 3.4 | 24 |
| 44 | Density of states of amorphous In-Ga-Zn-O from electrical and optical characterization. <i>Journal of Applied Physics</i> , 2014 , 116, 154505 | 2.5 | 44 |
| 43 | Unified Subthreshold Coupling Factor Technique for Surface Potential and Subgap Density-of-States in Amorphous Thin Film Transistors. <i>IEEE Electron Device Letters</i> , 2013 , 34, 641-643 | 4.4 | 17 |
| 42 | A novel SiNW/CMOS hybrid biosensor for high sensitivity/low noise 2013 , | | 6 |
| 41 | SiNW-CMOS Hybrid Common-Source Amplifier as a Voltage-Readout Hydrogen Ion Sensor. <i>IEEE Electron Device Letters</i> , 2013 , 34, 135-137 | 4.4 | 13 |
| 40 | Analytical Current and Capacitance Models for Amorphous Indium-Gallium-Zinc-Oxide Thin-Film Transistors. <i>IEEE Transactions on Electron Devices</i> , 2013 , 60, 3465-3473 | 2.9 | 27 |
| 39 | Characterization of density-of-states and parasitic resistance in a-InGaZnO thin-film transistors after negative bias stress. <i>Applied Physics Letters</i> , 2013 , 102, 143502 | 3.4 | 15 |
| 38 | 10.2: Invited Paper: Development of Oxide TFTs Structures. <i>Digest of Technical Papers SID International Symposium</i> , 2013 , 44, 89-92 | 0.5 | 34 |
| 37 | Cation composition effects on electronic structures of In-Sn-Zn-O amorphous semiconductors. <i>Journal of Applied Physics</i> , 2013 , 113, 183706 | 2.5 | 45 |
| 36 | High performance gallium-zinc oxynitride thin film transistors for next-generation display applications 2013 , | | 23 |
| 35 | Extraction of the Channel Mobility in InGaZnO TFTs Using Multifrequency Capacitance/Voltage Method. <i>IEEE Electron Device Letters</i> , 2012 , 33, 815-817 | 4.4 | 4 |
| 34 | Impact of Oxygen Flow Rate on the Instability Under Positive Bias Stresses in DC-Sputtered Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 62-64 | 4.4 | 57 |
| 33 | 9.4L: Late-News Paper: Microscopic Mechanism of the Negative Bias and Illumination Stress Instability of Amorphous Oxide TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2012 , 43, 95-97 | 0.5 | |
| 32 | Complementary Silicon Nanowire Hydrogen Ion Sensor With High Sensitivity and Voltage Output. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1768-1770 | 4.4 | 21 |
| 31 | Differential Ideality Factor Technique for Extraction of Subgap Density of States in Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 399-401 | 4.4 | 37 |
| 30 | Modified Conductance Method for Extraction of Subgap Density of States in a-IGZO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2012 , 33, 1138-1140 | 4.4 | 22 |

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| 29 | Production of β -carotene and acetate in recombinant <i>Escherichia coli</i> with or without mevalonate pathway at different culture temperature or pH. <i>Biotechnology and Bioprocess Engineering</i> , 2012 , 17, 1196-1204 | 3.1 | 7 |
| 28 | Instability of amorphous oxide semiconductors via carrier-mediated structural transition between disorder and peroxide state. <i>Physica Status Solidi (B): Basic Research</i> , 2012 , 249, 1277-1281 | 1.3 | 97 |
| 27 | Amorphous InGaZnO Thin-Film Transistors Part I: Complete Extraction of Density of States Over the Full Subband-Gap Energy Range. <i>IEEE Transactions on Electron Devices</i> , 2012 , 59, 2689-2698 | 2.9 | 49 |
| 26 | P-202L: Late-News Poster: Density-of-States Based Analysis on the Effect of Active Thin-film Thickness on Current Stress-induced Instability in Amorphous InGaZnO AMOLED Driver TFTs. <i>Digest of Technical Papers SID International Symposium</i> , 2011 , 42, 1223-1226 | 0.5 | 1 |
| 25 | Extraction of Separated Source and Drain Resistances in Amorphous Indium-Gallium-Zinc Oxide TFTs Through $\Delta C/\Delta V$ Characterization. <i>IEEE Electron Device Letters</i> , 2011 , 32, 761-763 | 4.4 | 22 |
| 24 | The Effect of the Active Layer Thickness on the Negative Bias Stress-Induced Instability in Amorphous InGaZnO Thin-Film Transistors. <i>IEEE Electron Device Letters</i> , 2011 , 32, 1388-1390 | 4.4 | 15 |
| 23 | Design of Noncoplanar Diagonal Electrode Structure for Oxide Thin-Film Transistor. <i>IEEE Electron Device Letters</i> , 2011 , 32, 39-41 | 4.4 | 3 |
| 22 | Modeling and Separate Extraction of Gate-Bias- and Channel-Length-Dependent Intrinsic and Extrinsic Source/Drain Resistances in MOSFETs. <i>IEEE Electron Device Letters</i> , 2011 , 32, 722-724 | 4.4 | 8 |
| 21 | Comparative study of quasi-static and normal capacitance-voltage characteristics in amorphous Indium-Gallium-Zinc-Oxide thin film transistors. <i>Solid-State Electronics</i> , 2011 , 56, 95-99 | 1.7 | 14 |
| 20 | Origin of threshold voltage shift by interfacial trap density in amorphous InGaZnO thin film transistor under temperature induced stress. <i>Applied Physics Letters</i> , 2011 , 99, 062108 | 3.4 | 36 |
| 19 | Effect of interface states on the instability under temperature stress in amorphous SiInZnO thin film transistor. <i>Applied Physics Letters</i> , 2011 , 99, 162101 | 3.4 | 10 |
| 18 | Origin of instability by positive bias stress in amorphous Si-In-Zn-O thin film transistor. <i>Applied Physics Letters</i> , 2011 , 99, 172106 | 3.4 | 18 |
| 17 | Effect of channel thickness on density of states in amorphous InGaZnO thin film transistor. <i>Applied Physics Letters</i> , 2011 , 98, 122105 | 3.4 | 89 |
| 16 | Low-frequency noise in amorphous indium-gallium-zinc oxide thin-film transistors from subthreshold to saturation. <i>Applied Physics Letters</i> , 2010 , 97, 122104 | 3.4 | 26 |
| 15 | Extraction of Subgap Density of States in Amorphous InGaZnO Thin-Film Transistors by Using Multifrequency Capacitance-Voltage Characteristics. <i>IEEE Electron Device Letters</i> , 2010 , 31, 231-233 | 4.4 | 127 |
| 14 | P-205L: Late-News Poster: Comparison between a-InGaZnO and a-InHfZnO TFTs in Perspective of Subgap Density of States (DOS) in Active Film. <i>Digest of Technical Papers SID International Symposium</i> , 2010 , 41, 1389 | 0.5 | 2 |
| 13 | Separate Extraction of Source, Drain, and Substrate Resistances in MOSFETs With Parasitic Junction Current Method. <i>IEEE Electron Device Letters</i> , 2010 , | 4.4 | 7 |
| 12 | P-203L: Late-News Poster: Analysis on AC Stress-Induced Degradation Mechanism of Amorphous Indium-Gallium-Zinc-Oxide Thin Film Transistor Inverters. <i>Digest of Technical Papers SID International Symposium</i> , 2010 , 41, 1380 | 0.5 | |

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| 11 | Subgap Density-of-States-Based Amorphous Oxide Thin Film Transistor Simulator (DeAOTS). <i>IEEE Transactions on Electron Devices</i> , 2010 , 57, 2988-3000 | 2.9 | 55 |
| 10 | Highly stable transparent amorphous oxide semiconductor thin-film transistors having double-stacked active layers. <i>Advanced Materials</i> , 2010 , 22, 5512-6 | 24 | 113 |
| 9 | Electrical stress-induced instability of amorphous indium-gallium-zinc oxide thin-film transistors under bipolar ac stress. <i>Applied Physics Letters</i> , 2009 , 95, 132101 | 3.4 | 33 |
| 8 | Production of β -carotene by recombinant <i>Escherichia coli</i> with engineered whole mevalonate pathway in batch and fed-batch cultures. <i>Biotechnology and Bioprocess Engineering</i> , 2009 , 14, 559-564 | 3.1 | 17 |
| 7 | Sub-1-V-Output CMOS bandgap reference circuit with small area and low power consumption. <i>IEICE Electronics Express</i> , 2009 , 6, 161-166 | 0.5 | 3 |
| 6 | Extraction of Density of States in Amorphous GaInZnO Thin-Film Transistors by Combining an Optical Charge Pumping and Capacitance-Voltage Characteristics. <i>IEEE Electron Device Letters</i> , 2008 , 29, 1292-1295 | 4.4 | 46 |
| 5 | Modeling of amorphous InGaZnO thin-film transistors based on the density of states extracted from the optical response of capacitance-voltage characteristics. <i>Applied Physics Letters</i> , 2008 , 93, 182102 | 3.4 | 84 |
| 4 | Channel width dependence of hot electron injection program/hot hole erase cycling behavior in silicon-oxide-nitride-oxide-silicon (SONOS) memories. <i>Solid-State Electronics</i> , 2008 , 52, 844-848 | 1.7 | 2 |
| 3 | Excessive Oxygen Peroxide Model-Based Analysis of Positive-Bias-Stress and Negative-Bias-Illumination-Stress Instabilities in Self-Aligned Top-Gate Coplanar InGaZnO Thin-Film Transistors. <i>Advanced Electronic Materials</i> , 2101062 | 6.4 | 4 |
| 2 | Estimation of melatonin level and core body temperature: heart rate and heart rate variability as circadian rhythm markers. <i>Biological Rhythm Research</i> , 1-18 | 0.8 | 0 |
| 1 | All-Solution-Processed Carbon Nanotube Floating Gate Memories. <i>ACS Applied Nano Materials</i> , | 5.6 | 0 |